

SiGe Rectification Process

Abstract of the Disclosure

A method for forming strain-relaxed SiGe films comprises depositing a graded strained SiGe layer on a substrate in which the concentration of Ge is greater at the interface with the substrate than at the top of the layer. The strained SiGe film is subsequently oxidized, producing a strain-relaxed SiGe film with a substantially uniform Ge concentration across the thickness of the film. The relaxed SiGe layer may be used to form a strained silicon layer on a substrate.

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